March 2001 Revised August 2001

FAIRCHILD

SEMICONDUCTOR

74LVTH16500 Low Voltage 18-Bit Universal Bus Transceivers with Bushold and 3-STATE Outputs

General Description

The LVTH16500 is an 18-bit universal bus transceiver combining D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Data flow in <u>each</u> direction is controlled by output-enable (OEAB and OEBA), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs.

The LVTH16500 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

The transceiver is designed for low voltage (3.3V) $V_{\rm CC}$ applications, but with the capability to provide a TTL interface to a 5V environment. The LVTH16500 is fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining low power dissipation.

Features

- \blacksquare Input and output interface capability to systems at 5V V_{CC}
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs
- Live insertion/extraction permitted
- Power up/down high impedance provides glitch-free bus loading
- Outputs source/sink -32 mA/+64 mA
- Functionally compatible with the 74 series 16500
- ESD Performance:
- Human-Body Model > 2000V Machine Model > 200V
- Charged-Device Model > 1000V
- Also packaged in plastic Fine-Pitch Ball Grid Array (FBGA) (Preliminary)

Ordering Code:

Order Number	Package Number	Package Description
74LVTH16500GX (Note 1)	BGA54A (Preliminary)	54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide [TAPE and REEL]
74LVTH16500MEA (Note 2)	MS56A	56-Lead Shrink Small Outline Package (SSOP), JEDEC MO-118, 0.300" Wide
74LVTH16500MTD (Note 2)	MTD56	56-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide

Note 1: BGA package available in Tape and Reel only.

Note 2: Devices also available in Tape and Reel. Specify by appending the suffix "X" to the ordering code.

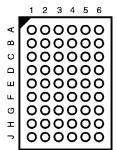
74LVTH16500

Connection Diagrams

Pin Assignment for SSOP and TSSOP

Assignin	inent i	01 3301	c	
1				1
0EAB —	1	<u> </u>	56	— GND
LEAB —	2	ę	55	- CLKAB
A1	3	Ę	54	— B ₁
GND —	4	5	53	— GND
A2 -	5	Ę	52	— В ₂
A3 —	6	1	51	— В ₃
v _{cc} —	7	5	50	−v _{cc}
A4 —	8	4	\$9	— B ₄
A ₅ —	9	4	18	— В ₅
А ₆ —	10	4	\$7	— В ₆
gnd —	11	4	\$6	— GND
A ₇ —	12	4	45	— в ₇
A ₈ —	13	4	44	— В ₈
A ₉ —	14	4	43	— В ₉
A ₁₀ —	15	4	\$2	- B ₁₀
A ₁₁ —	16		41	— ^в 1 1
A ₁₂ —	17	4	40	-B ₁₂
GND —	18	1	39	— GND
A ₁₃ —	19	3	38	- B _{1 3}
A ₁₄ —	20	3	37	- B ₁₄
A ₁₅ —	21	3	36	— B ₁₅
v _{cc} —	22	3	35	−v _{cc}
A ₁₆ —	23	3	54	— B ₁₆
A ₁₇ —	24		33	- B ₁₇
GND —	25	3	52	— GND
A ₁₈ —	26	:	31	— B ₁₈
ОЕВА —	27	3	30	- CLKBA
LEBA —	28	2	29	— GND

Pin Assignment for FBGA



(Top Thru View)

Pin Descriptions

Pin Names	Description
A ₁ -A ₁₈	Data Register A Inputs/3-STATE Outputs
B ₁ -B ₁₈	Data Register B Inputs/3-STATE Outputs
CLKAB, CLKBA	Clock Pulse Inputs
LEAB, LEBA	Latch Enable Inputs
OEAB, OEBA	Output Enable Inputs

FBGA Pin Assignments

	1	2	3	4	5	6
Α	A ₂	A ₁	OEAB	GND	B ₁	B ₂
в	A ₄	A ₃	LEAB	CLKAB	B ₃	B ₄
С	A ₆	A ₅	V _{CC}	V _{CC}	В ₅	B ₆
D	A ₈	A ₇	GND	GND	B ₇	B ₈
Е	A ₁₀	A ₉	GND	GND	B ₉	B ₁₀
F	A ₁₂	A ₁₁	GND	GND	В ₁₁	B ₁₂
G	A ₁₄	A ₁₃	V _{CC}	V _{CC}	B ₁₃	B ₁₄
н	A ₁₆	A ₁₅	OEAB	CLKBA	B ₁₅	B ₁₆
J	A ₁₇	A ₁₈	LEBA	GND	B ₁₈	B ₁₇

Function Table (Note 3)

	Inp	outs		Output
OEAB	LEAB	CLKAB	An	B _n
L	Х	Х	Х	Z
Н	н	Х	L	L
Н	н	Х	н	н
Н	L	\downarrow	L	L
н	L	\downarrow	н	н
н	L	н	х	B ₀ (Note 4)
Н	L	L	Х	B ₀ (Note 4) B ₀ (Note 5)
= HIGH Volta	ige Level	L = LOW V	oltage Lev	el

H = HIGH Voltage Level X = Immaterial Z = $\downarrow = HIGH$ -to-LOW Clock Transition Z = High Impedance

Note 3: A-to-B data flow is shown: B-to-A flow is similar but uses \overline{OEBA} , LEBA, and \overline{CLKBA} . \overline{OEBA} is active LOW.

Note 4: Output level before the indicated steady-state input conditions were established.

Note 5: Output level before the indicated steady-state input conditions were established, provided that CLKAB was LOW before LEAB went LOW.

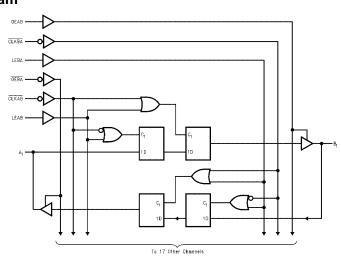
Functional Description

For A-to-B data flow, the device operates in the transparent mode when LEAB is HIGH. When LEAB is LOW, the A data is latched if CLKAB is held at a HIGH or LOW logic level. If LEAB is LOW, the A bus data is stored in the latch/flip-flop on the HIGH-to-LOW transition of CLKAB. Output-enable OEAB is active-HIGH. When OEAB is

Logic Diagram

HIGH, the outputs are active. When OEAB is LOW, the outputs are in the high-impedance state.

Data flow for B-to-A is similar to that of A-to-B but uses OEBA, LEBA, and CLKBA. The output enables are complementary (OEAB is active-HIGH and OEBA is active-LOW).



0
0
ŝ
ဖ
Υ_
Т
F
>
-
4
~

Absolute Maximum Ratings(Note 6)

Symbol	Parameter	Value	Conditions	Units
V _{cc}	Supply Voltage	-0.5 to +4.6		V
/1	DC Input Voltage	-0.5 to +7.0		V
/o	DC Output Voltage	-0.5 to +7.0	Output in 3-STATE	V
		-0.5 to +7.0	Output in HIGH or LOW State (Note 7)	V
IK	DC Input Diode Current	-50	V _I < GND	mA
OK	DC Output Diode Current	-50	V _O < GND	mA
0	DC Output Current	64	V _O > V _{CC} Output at HIGH State	
		128	V _O > V _{CC} Output at LOW State	mA
00	DC Supply Current per Supply Pin	±64		mA
GND	DC Ground Current per Ground Pin	±128		mA
STG	Storage Temperature	-65 to +150		°C

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V _{CC}	Supply Voltage	2.7	3.6	V
VI	Input Voltage	0	5.5	V
I _{ОН}	HIGH-Level Output Current		-32	mA
I _{OL}	LOW-Level Output Current		64	mA
T _A	Free-Air Operating Temperature	-40	85	°C
$\Delta t / \Delta V$	Input Edge Rate, V _{IN} = 0.8V - 2.0V, V _{CC} = 3.0V	0	10	ns/V

Note 6: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied. Note 7: I_O Absolute Maximum Rating must be observed.

Symbol	Parameter		v _{cc}	T _A = -40° C to $+85^{\circ}$ C		Units	Conditions
-	i arameter		(V)	Min	Max	Unita	Conditiona
V _{IK}	Input Clamp Diode Voltage		2.7		-1.2	V	I _I = -18 mA
VIH	Input HIGH Voltage		2.7–3.6	2.0		V	$V_0 \le 0.1V$ or
V _{IL}	Input LOW Voltage		2.7–3.6		0.8	v	$V_O \ge V_{CC} - 0.1V$
V _{OH}	Output HIGH Voltage		2.7–3.6	V _{CC} - 0.2		V	I _{OH} = -100 μA
			2.7	2.4		V	I _{OH} = -8 mA
		Γ	3.0	2.0		V	I _{OH} = -32 mA
V _{OL}	Output LOW Voltage		2.7		0.2	V	I _{OL} = 100 μA
			2.7		0.5	V	I _{OL} = 24 mA
			3.0		0.4	V	I _{OL} = 16 mA
			3.0		0.5	V	I _{OL} = 32 mA
		Γ	3.0		0.55	V	I _{OL} = 64 mA
I _{I(HOLD)}	Bushold Input Minimum Drive		3.0	75		μΑ	$V_{I} = 0.8V$
			5.0	-75		μΑ	$V_{I} = 2.0V$
I _{I(OD)}	Bushold Input Over-Drive		3.0	500		μΑ	(Note 8)
	Current to Change State		5.0	-500		μΑ	(Note 9)
l _l	Input Current		3.6		10	μΑ	V _I = 5.5V
	Co	ontrol Pins	3.6		±1	μΑ	$V_I = 0V \text{ or } V_{CC}$
	D	ata Pins	3.6		-5	μΑ	$V_I = 0V$
		ata 1 1113	5.0		1	μΑ	$V_I = V_{CC}$
I _{OFF}	Power Off Leakage Current		0		±100	μΑ	$0V \le V_1 \text{ or } V_0 \le 5.5V$
I _{PU/PD}	Power Up/Down 3-STATE	0–1.5V		±100	μA	V _O = 0.5V to 3.0V	
	Output Current		0 1.01		100	μι	$V_I = GND \text{ or } V_{CC}$
I _{OZL}	3-STATE Output Leakage Curren	nt	3.6		-5	μΑ	$V_{O} = 0.0V$
I _{OZH}	3-STATE Output Leakage Curren	nt	3.6		5	μΑ	V _O = 3.6V
I _{OZH} +	3-STATE Output Leakage Curren	nt	3.6		10	μΑ	$V_{CC} < V_O \le 5.5 V$
I _{CCH}	Power Supply Current		3.6		0.19	mA	Outputs HIGH
I _{CCL}	Power Supply Current		3.6		5	mA	Outputs LOW
I _{CCZ}	Power Supply Current		3.6		0.19	mA	Outputs Disabled
I _{CCZ} +	Power Supply Current		3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V$, Outputs Disabled
ΔI_{CC}	Increase in Power Supply Curren (Note 10)	nt	3.6		0.2	mA	One Input at V _{CC} – 0.6V Other Inputs at V _{CC} or GND

Note 8: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 9: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Note 10: This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

Dynamic Switching Characteristics (Note 11)

Symbol	Parameter	V_{CC} $T_A = 25^{\circ}C$		Units	Conditions		
Symbol	Farameter	(V)	Min	Тур	Max	Units	$\textbf{C}_{\textbf{L}}=\textbf{50}~\textbf{pF},~\textbf{R}_{\textbf{L}}=\textbf{500}\Omega$
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3		0.8		V	(Note 12)
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3		-0.8		V	(Note 12)

Note 11: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 12: Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW.

0
0
Ō
ဖ
ς_
Т
F
>
-
4
N

AC Electrical Characteristics

			$T_A = -40^{\circ}C$	to +85°C, 0	C _L = 50 pF,	$R_L = 500 \Omega$	
Symbol	Param	neter	V _{CC} = 3.	$3\pm0.3V$	V _{CC} =	= 2.7V	Units
			Min	Max	Min	Max	
f _{MAX}	CLKAB or CLKBA to B or A		150		150		MHz
t _{PLH}	Propagation Delay		1.3	5.2	1.3	5.8	
t _{PHL}	Data to Outputs		1.3	4.7	1.3	5.3	ns
t _{PLH}	Propagation Delay		1.5	5.5	1.5	6.3	ns
t _{PHL}	LEBA or LEAB to B or A	1.5	5.1	1.5	5.7	115	
t _{PLH}	Propagation Delay	1.3	5.8	1.3	6.9	ns	
t _{PHL}	CLKBA or CLKAB to B or A			5.0	1.3	5.9	115
t _{PZH}	Output Enable Time			5.0	1.3	5.7	ns
t _{PZL}			1.3	5.5	1.3	6.5	115
t _{PHZ}	Output Disable Time			6.0	1.7	6.7	ns
t _{PLZ}			1.6	5.8	1.7	6.3	115
t _{SU}	Setup Time	A before CLKAB	2.9		2.9		
		B before CLKBA	2.9		2.9		
		A or B before LE, CLK HIGH	1.8		0.9		ns
		A or B before LE, CLK LOW	2.9		2.3		
t _H	Hold Time	A or B after CLK	0.5		0.9		ns
		A or B after LE	1.6		1.6		115
t _W	Pulse Duration	LE HIGH	3.3		3.3		20
		CLK HIGH or LOW	3.3		3.3		ns
t _{OSLH}	Output to Output Skew (Note 13)			1.0		1.0	00
t _{OSHL}				1.0		1.0	ns

Note 13: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}).

Capacitance (Note 14)

Symbol	Parameter	Conditions	Typical	Units
C _{IN}	Input Capacitance	$V_{CC} = 0V, V_I = 0V \text{ or } V_{CC}$	4	pF
C _{I/O}	Input/Output Capacitance	$V_{CC} = 3.0V$, $V_O = 0V$ or V_{CC}	8	pF

Note 14: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883, Method 3012.

